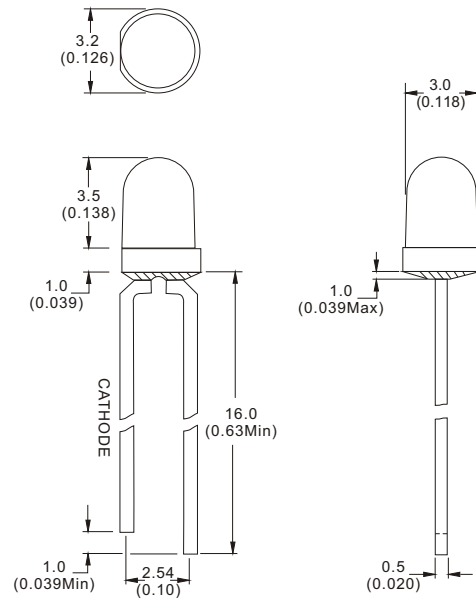




● Features:

- 1. Chip material: Silicon
- 2. Emitting color: Photo Diode
- 3. Lens Appearance: Water Clear
- 4. Long life-solid state reliability
- 5. IC compatible/Low current capability
- 6. RoHS compliant

● Package dimensions



Notes:

- 1. All dimensions are in millimeters (inches).
- 2. Tolerance is $\pm 0.25\text{mm}$ ($0.01''$) unless otherwise specified.
- 3. An epoxy meniscus may extend about 1.0mm down to the lead.
- 4. Specifications are subject to change without notice.

● Absolute maximum ratings ($T_a = 25^\circ\text{C}$)

Characteristic	Test Condition	Symbol	PT	Units
Reverse Breakdown Voltage		V_{BR}	60	V
Power Dissipation		P_D	100	mW
Operating Temperature		T_{OPR}	-40 to +80	$^\circ\text{C}$
Storage Temperature		T_{STG}	-40 to +85	$^\circ\text{C}$
Lead Soldering Temperature	1.60mm from body maximum 3 seconds	T_{SOL}	260	$^\circ\text{C}$



● Electrical And Optical Characteristics(Ta=25°C)

Parameter	Test Condition	Symbol	Min.	Typ.	Max.	Units
Light Current	V _R =5V H=5mw/cm ² @940nm	I _L	500	---	2000	μA
Reverse Dark Current	V _R =10V H=0mw/cm	I _D	---	---	100	nA
Collector-Emitter Breakdown Voltage	I _{CEO} =100μA	V _{BR CEO}	30	---	---	V
Emitter-Collector Breakdown Voltage	I _{ECO} =100μA	V _{BR ECO}	5	---	---	V
Collector-Base Breakdown Voltage	I _{EBO} =100μA	V _{BR CBO}	40	---	---	V
Collector-Emitter Stauration Voltage	I _B =1mA I _C =2mA	V _{CE(SAT)}	---	0.2	0.4	V
Peak Sensing Wavelengh		λ _p	---	940	---	nm
Rise Time Fall Time	R _L =50Ω V _R =20V	tr tf	---	5	---	μs